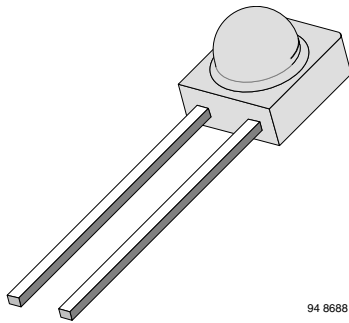


High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



DESCRIPTION

TSSF4500 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (L x W x H in mm): 4.5 x 4 x 4.8
- Peak wavelength: $\lambda_p = 890$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\phi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 12$ MHz
- Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



Note

** Please see document "Vishay Material Category Policy":
www.vishay.com/doc?99902

APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- TSSF4500 is ideal for the design of transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY				
COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
TSSF4500	20	± 22	890	30

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSSF4500	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5\text{ s}$, 2 mm from case	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient	Leads not soldered	R_{thJA}	450	K/W

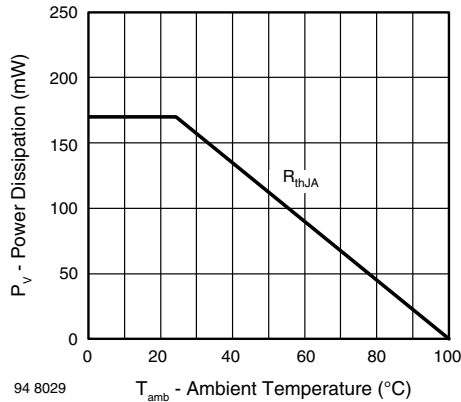


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

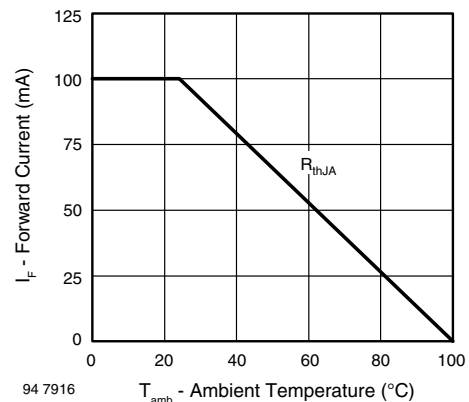


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F		1.35	1.6	V
	$I_F = 1.5\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F		2.4		V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{V_F}		- 1.8		mV/K
Reverse current	$V_R = 5\text{ V}$	I_R			10	μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_j		160		pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	10	20	50	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e		200		mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e		35		mW
Temperature coefficient of ϕ_e	$I_F = 100\text{ mA}$	TK_{ϕ_e}		- 0.7		%/K
Angle of half intensity		ϕ		± 22		deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p		890		nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		40		nm
Temperature coefficient of λ_p	$I_F = 100\text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100\text{ mA}$	t_r		30		ns
Fall time	$I_F = 100\text{ mA}$	t_f		30		ns
Cut-off frequency	$I_{DC} = 70\text{ mA}$, $I_{AC} = 30\text{ mA pp}$	f_c		12		MHz
Virtual source diameter		d		2.1		mm

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

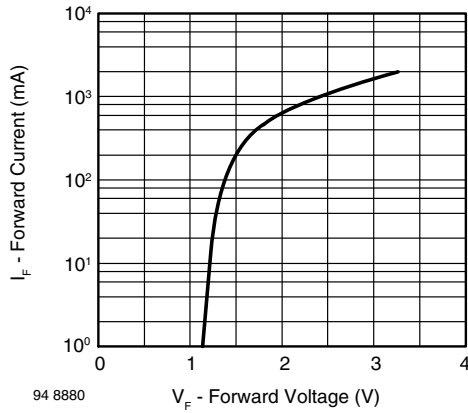


Fig. 3 - Forward Current vs. Forward Voltage

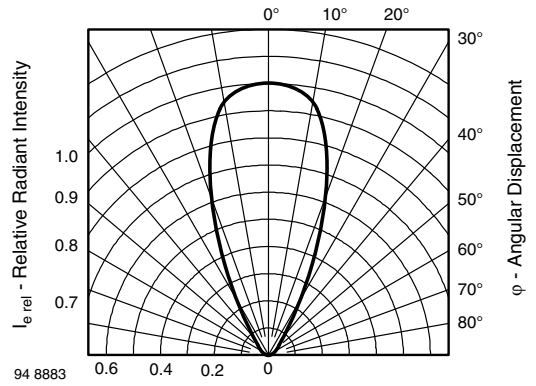


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

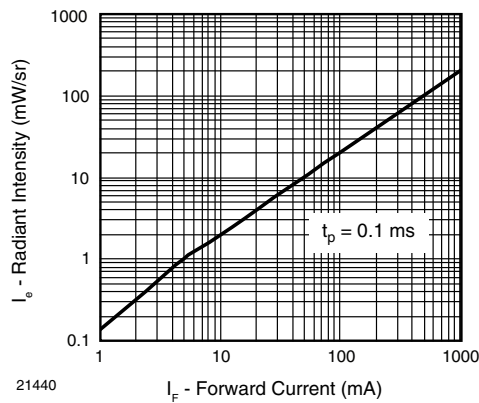


Fig. 4 - Radiant Intensity vs. Forward Current

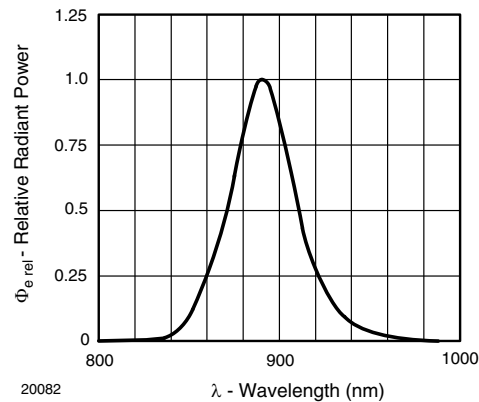
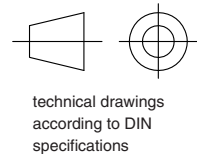
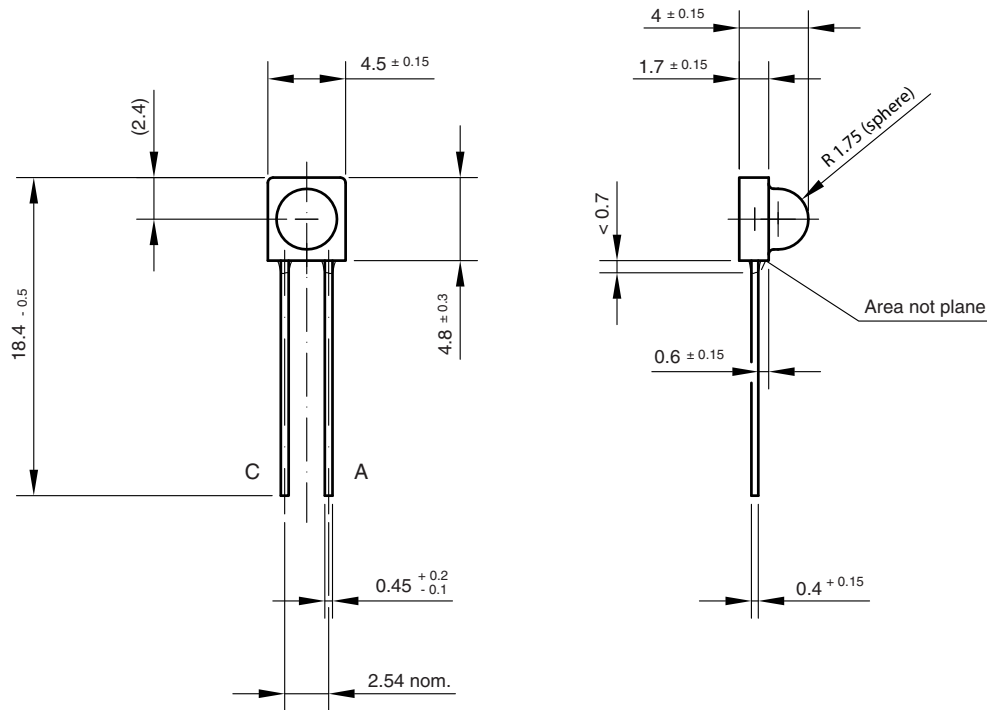


Fig. 5 - Relative Radiant Power vs. Wavelength



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5253.01-4

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